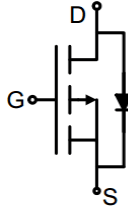
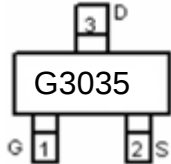
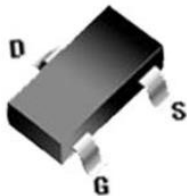


P-Channel Enhancement Mode Power MOSFET

Description The G3035 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.		 Schematic diagram	
General Features • V_{DS} -30V • I_D (at $V_{GS} = -10V$) -4.6A • $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 59mΩ • $R_{DS(ON)}$ (at $V_{GS} = -4.5V$) < 75mΩ • 100% Avalanche Tested • RoHS Compliant		 Marking and pin assignment	
Application • Power switch • DC/DC converters		 SOT-23	
Device	Package	Marking	Packaging
G3035	SOT-23	G3035	3000pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Continuous Drain Current	I_D	-4.6	A
Pulsed Drain Current (note1)	I_{DM}	-20	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

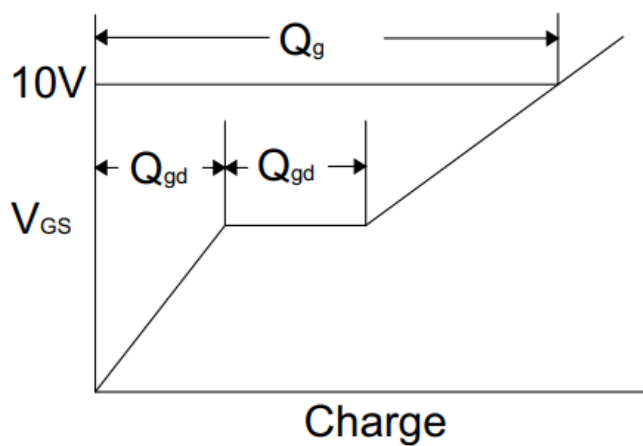
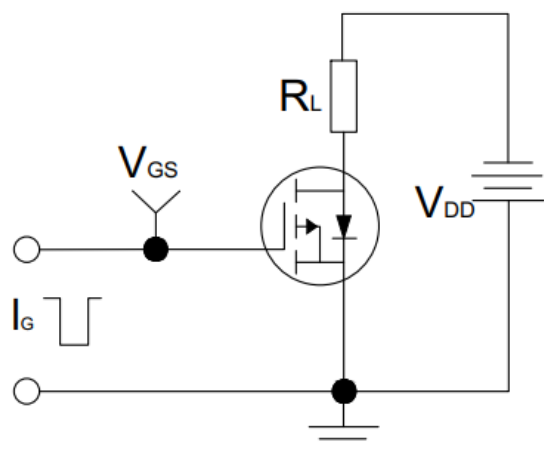
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	90	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	--	--	-1	uA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.5	-2	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -4A	--	50	59	mΩ
		V _{GS} = -4.5V, I _D = -3A	--	69	75	
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-4A	--	10	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -15V, f = 1.0MHz	--	650	--	pF
Output Capacitance	C _{oss}		--	105	--	
Reverse Transfer Capacitance	C _{rss}		--	65	--	
Total Gate Charge	Q _g	V _{DD} = -15V, I _D = -4.6A, V _{GS} = -10V	--	13	--	nC
Gate-Source Charge	Q _{gs}		--	2.8	--	
Gate-Drain Charge	Q _{gd}		--	2.7	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = -15V, I _D = -4A, R _G = 3Ω	--	9	--	ns
Turn-on Rise Time	t _r		--	5	--	
Turn-off Delay Time	t _{d(off)}		--	26	--	
Turn-off Fall Time	t _f		--	13	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	-4.6	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = -3A, V _{GS} = 0V	--	--	-1.2	V

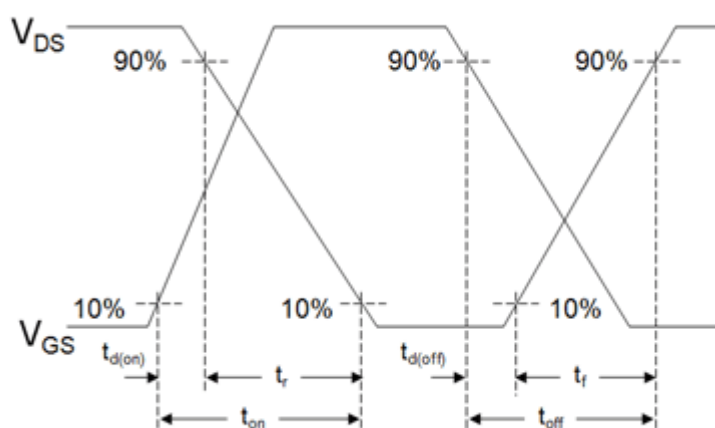
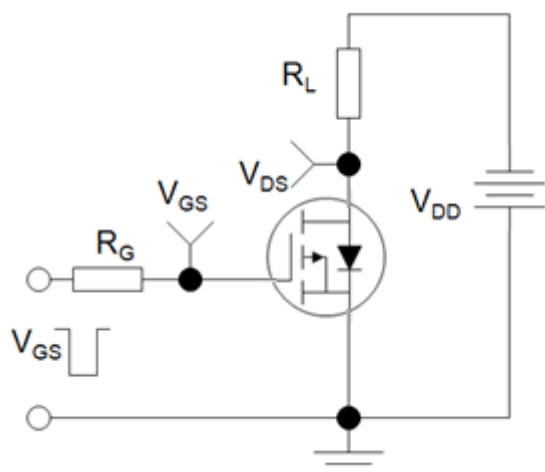
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

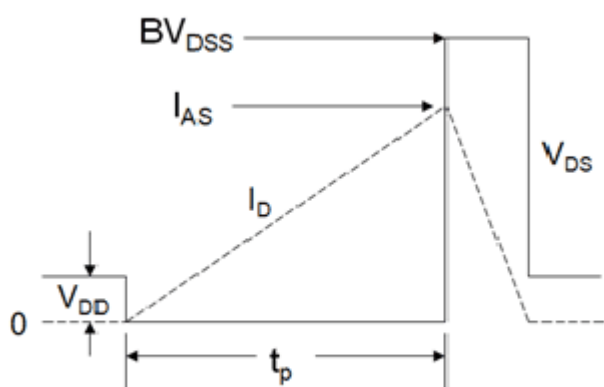
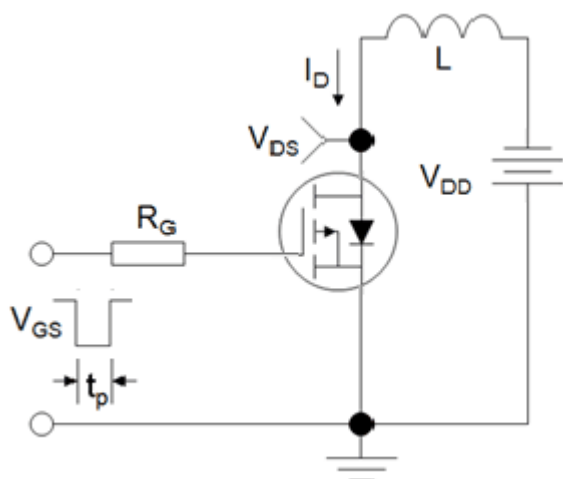
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

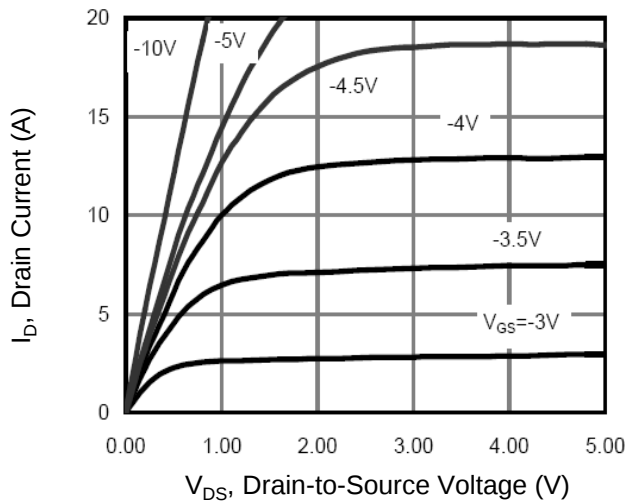


Figure 2. Transfer Characteristics

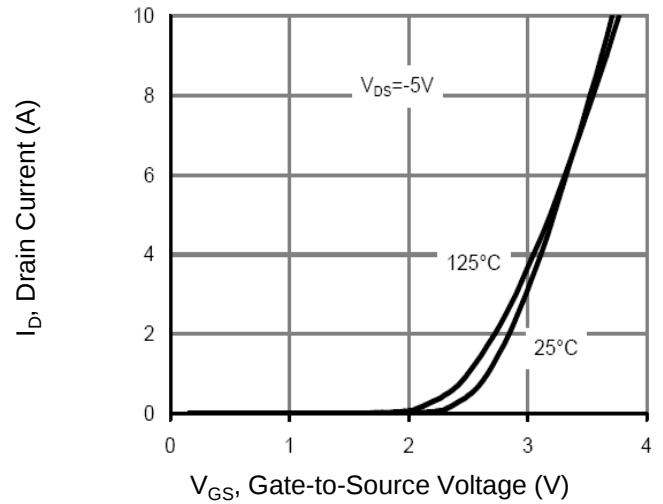


Figure 3. Gate Charge

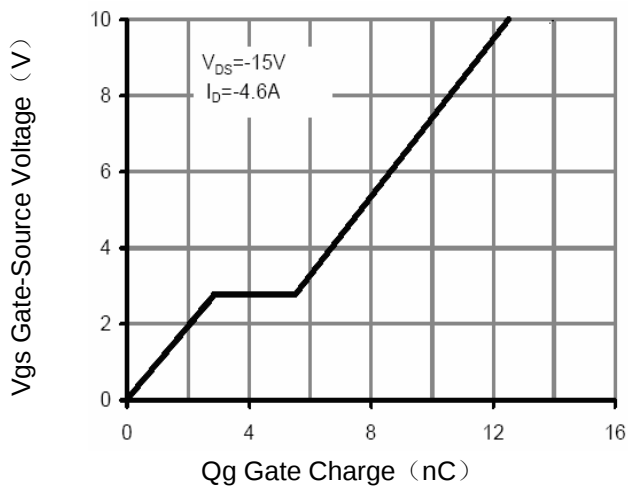


Figure 4. Drain Source On Resistance

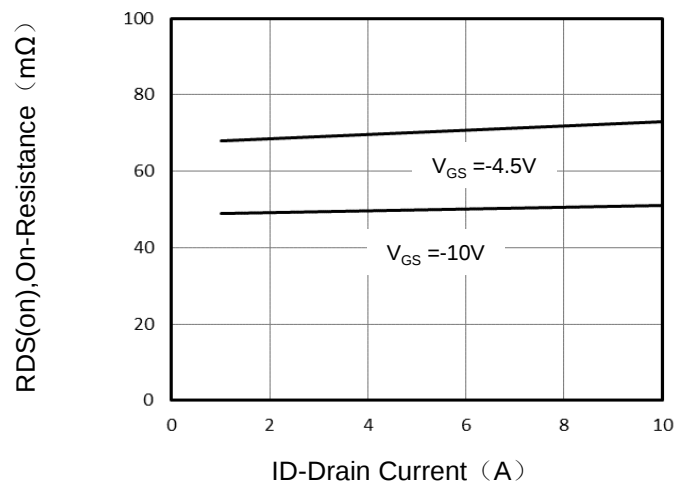


Figure 5. Capacitance

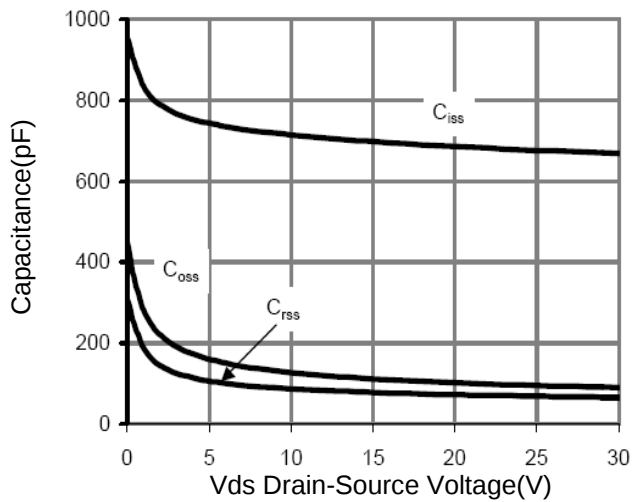
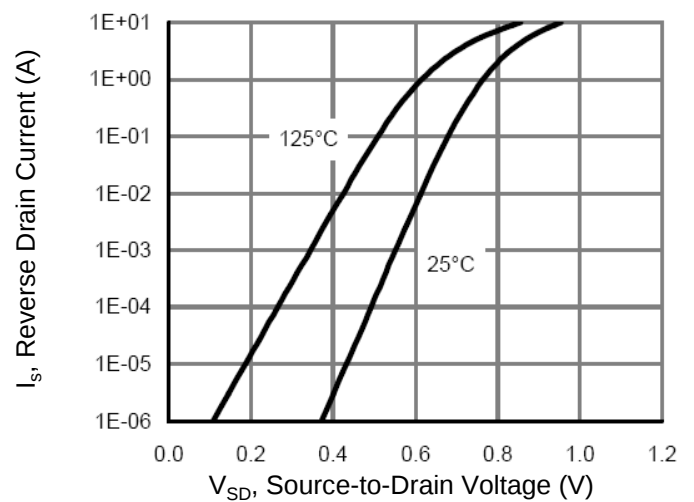


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

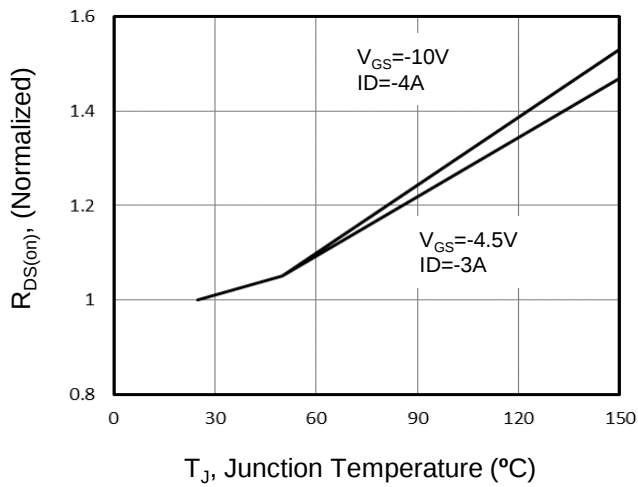


Figure 8. Safe Operation Area

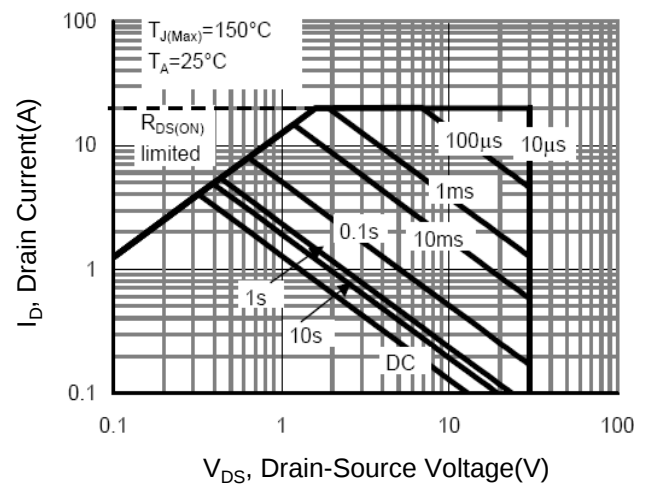
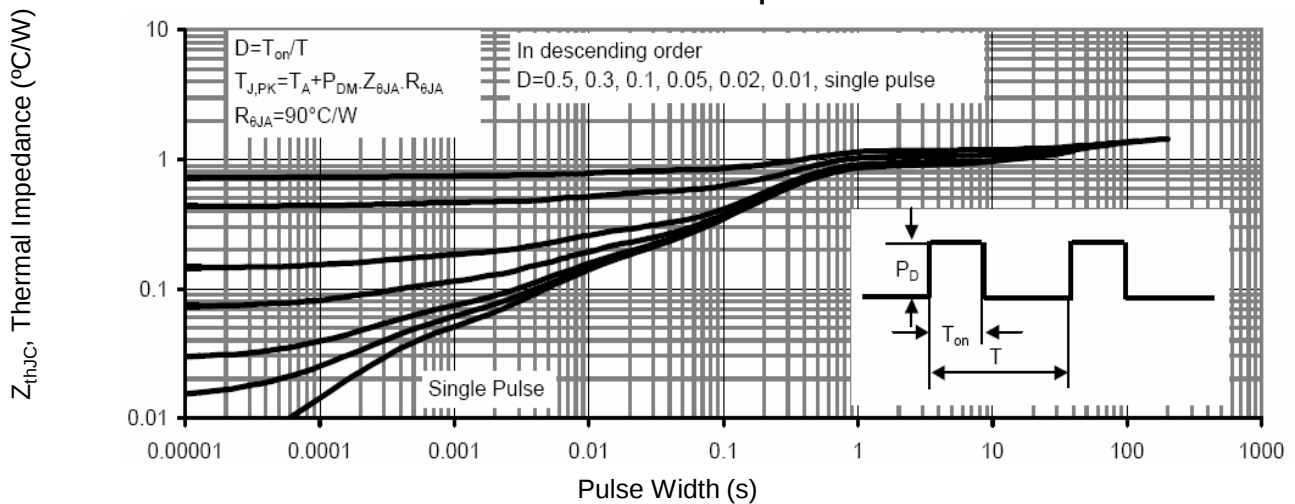
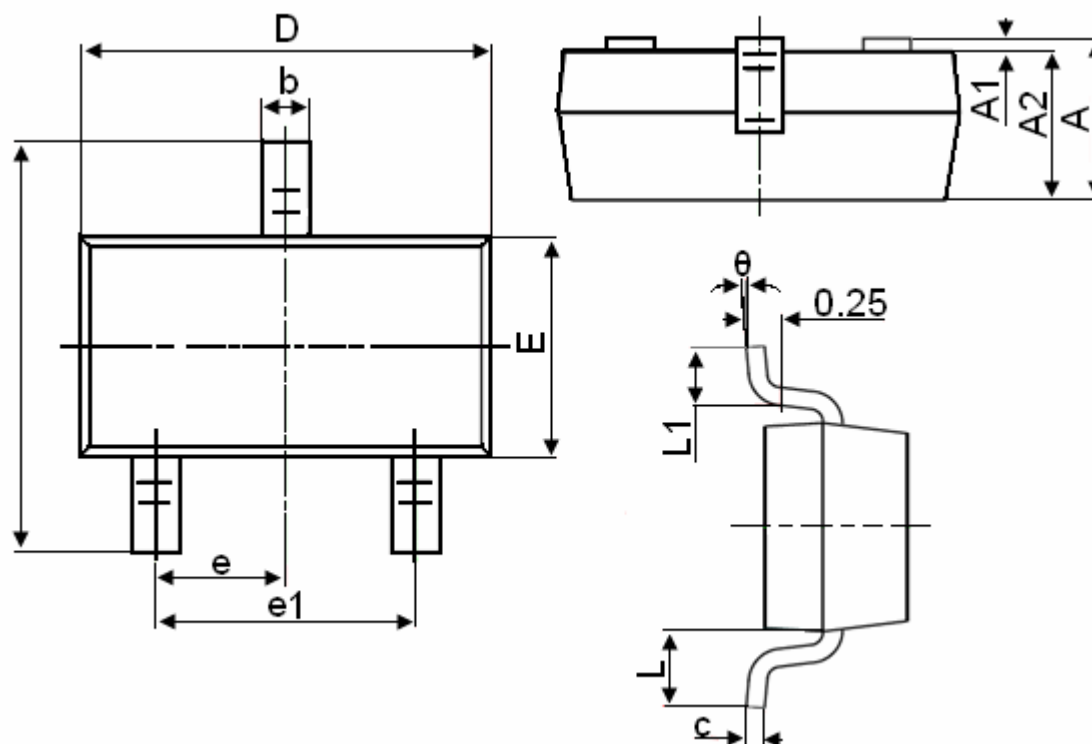


Figure 9. Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°